

# MA2Q736

## Silicon epitaxial planar type

For switching circuits

### ■ Features

- Forward current (average)  $I_{F(AV)}$ : 1 A type
- Reverse voltage (DC value)  $V_R$ : 40 V
- Allowing automatic insertion with the emboss taping

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

| Parameter                                   | Symbol      | Rating      | Unit             |
|---------------------------------------------|-------------|-------------|------------------|
| Reverse voltage (DC)                        | $V_R$       | 40          | V                |
| Repetitive peak reverse voltage             | $V_{RRM}$   | 40          | V                |
| Average forward current*1                   | $I_{F(AV)}$ | 1           | A                |
| Non-repetitive peak forward surge current*2 | $I_{FSM}$   | 30          | A                |
| Junction temperature                        | $T_j$       | -40 to +125 | $^\circ\text{C}$ |
| Storage temperature                         | $T_{stg}$   | -40 to +125 | $^\circ\text{C}$ |

Note) \*1 : With a printed-circuit board (copper foil area  $2\text{ mm} \times 2\text{ mm}$  or more on both cathode and anode sides)

\*2 : The peak-to-peak value in one cycle of 50 Hz sine-wave (non-repetitive)

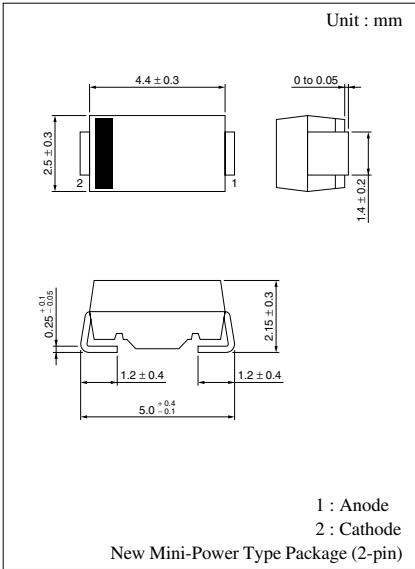
### ■ Electrical Characteristics $T_a = 25^\circ\text{C}$

| Parameter              | Symbol   | Conditions                                                             | Min | Typ | Max  | Unit |
|------------------------|----------|------------------------------------------------------------------------|-----|-----|------|------|
| Reverse current (DC)   | $I_R$    | $V_R = 40\text{ V}$                                                    |     |     | 2    | mA   |
| Forward voltage (DC)   | $V_F$    | $I_F = 1\text{ A}$                                                     |     |     | 0.55 | V    |
| Terminal capacitance   | $C_t$    | $V_R = 10\text{ V}, f = 1\text{ MHz}$                                  |     | 50  |      | pF   |
| Reverse recovery time* | $t_{rr}$ | $I_F = I_R = 100\text{ mA}$<br>$I_R = 10\text{ mA}, R_L = 100\ \Omega$ |     |     | 30   | ns   |

Note) 1. Schottky barrier diode is sensitive to electric shock (static electricity, etc.). Due attention must be paid on the charge of a human body and the leakage of current from the operating equipment

2. Rated input/output frequency: 20 MHz

3. \* :  $t_{rr}$  measuring instrument



Marking Symbol: PB

